

[METHOD FOR CONTROLLING LINEWIDTH IN ADVANCED LITHOGRA- PHY MASKS USING ELECTROCHEMISTRY]

Abstract

A method for controlling the linewidth of a feature formed within an advanced lithography mask includes electrochemically depositing an additive material on exposed sidewalls of an etched first layer of the mask, wherein the top of the etched first layer remains covered by a hardmask used during the etching of the first layer. A second layer beneath the etched first layer is resistant to the electrochemical deposition of the additive material thereupon.